WHAT IS CLAIMED IS:

1. An organic EL cell for preventing moisture that deteriorates the light-emitting characteristics of the organic EL cell, comprising:

a substrate;

a laminate structure formed on the substrate, wherein the laminate structure includes at least an anode, an organic light emitting layer, and a cathode;

a first sealing film formed on the laminate structure; and

a second sealing film formed on the first sealing film.

2. The organic EL cell of claim 1, wherein the first sealing film is an inorganic passivation film and the second sealing film is a resin film.

3. The organic EL cell of claim 2, further comprising a third sealing film formed on the second sealing film, wherein the third sealing film is an inorganic passivation film.

4. The organic EL cell of claim 3, wherein the first sealing film and the third sealing film are selected from a group consisting of silicon nitride, SiO_2, Al_2O_3, and diamond-like carbon (DLC).

5. The organic EL cell of claim 1, wherein the first sealing film is a resin film and the second sealing film is an inorganic passivation film.

6. The organic EL cell of claim 5, further comprising a third sealing film formed on the second film, wherein the third sealing film is a resin film.

7. The organic EL cell of claim 6, wherein the second sealing film is selected from a group consisting of silicon nitride, SiO_2, Al_2O_3, and diamond-like carbon (DLC).

8. The organic EL cell of claim 7, wherein the second sealing film is formed by vapor deposition.

9. The organic EL cell of claim 4, wherein the first sealing film and the third sealing flim are formed by vapor deposition.

10. A method for producing an organic EL cell for preventing moisture that deteriorates the light-emitting characteristics of the organic EL cell and that includes a substrate and a laminate structure formed on the substrate, wherein the laminate structure includes at least an anode, an organic light emitting layer, and a cathode, comprising the steps of forming a first sealing film on the laminate structure and forming a second sealing film on the first sealing film.

11. The method of claim 10, wherein the first sealing film is an inorganic passivation film and the second sealing film is a resin film.

12. The method of claim 11, further comprising the step of forming a third sealing film on the second sealing film, wherein the third sealing film is an inorganic passivation film.

13. The method of claim 12, wherein the first sealing film and the third sealing film are selected from a group consisting of silicon nitride, SiO_2, Al_2O_3, and diamond-like carbon (DLC).

14. The method of claim 10, wherein the first sealing film is a resin film and the second sealing film is an inorganic passivation film.

15. The method of claim 14, further comprising the step of forming a third sealing film on the second sealing film, wherein the third sealing film is a resin film.

16. The method of claim 15, wherein the second sealing film is selected from a group consisting of silicon nitride, SiO_2, Al_2O_3, and diamond-like carbon (DLC).

17. The method of claim 16, wherein the second sealing film is formed by vapor deposition.

18. The method of claim 13, wherein the first sealing film and the third sealing flim are formed by vapor deposition.

19. The method of 16, wherein the inorganic passivation film is that of silicon nitride formed by a plasma CVD.

20. The method of claim 19, wherein the silicon nitride is formed by the plasma CVD from a raw material gas composed only of silane and nitrogen.

21. The method of 13, wherein the inorganic passivation film is that of silicon nitride formed by a plasma CVD.

22. The method of claim 21, wherein the silicon nitride is formed by the plasma CVD from a raw material gas composed only of silane and nitrogen.